

Amendments to the Claims:

Although the following claims 1 – 43 are cancelled, we would like to make a few corrections for record purposes only.

1. (Cancelled) Apparatus for the treatment of disc-shaped substrates, especially semiconductor wafers, with a device for the rotation of the substrates (3) about an axis of rotation (A) and at least one first group (40; 60; 80) of nozzles, whereby the nozzles are differently spaced relative to the axis of rotation (A), characterized in that the nozzles can be controlled individually or in sub groups.
2. (Cancelled) Apparatus according to claim 1, characterized by at least one further group (44, 48; 62; 82) of nozzles, whereby the nozzles are differently spaced relative to the axis of rotation (A).
3. (Cancelled) Apparatus according to claim 2, characterized in that the nozzles of the further group (44, 48; 62; 82) can be controlled individually or in sub groups.
4. (Cancelled) Apparatus according to claim 2 or 3, characterized in that three groups (40, 44, 48) are provided.
5. (Cancelled) Apparatus according to one of the claims 2 to 4, characterized in that nozzles of at least one further group (44, 48, 62; 82) are, with regard to the spacing relative to the axis of rotation (A), offset relative to the nozzles of the first group (40; 60; 80).

6. (Cancelled) Apparatus according to one of the preceding claims, characterized in that nozzles of at least one group (40, 44, 48; 60, 62; 80) are disposed along a straight line that extends radially relative to the axis of rotation (A).
7. (Cancelled) Apparatus according to claim 6, characterized in that the nozzles of at least two groups (44, 48; 60, 62; 80, 82) are disposed along a common straight line.
8. (Cancelled) Apparatus according to claim 7, characterized in that the nozzles of one group (44, 48; 60, 62; 80, 82) are disposed between the nozzles of the other group (48, 44; 62, 60; 82, 80).
9. (Cancelled) Apparatus according to one of the preceding claims, characterized in that the nozzles of at least one group (40, 44, 48; 60, 62; 80, 82) can be supplied with fluid via a common fluid supply unit.
10. (Cancelled) Apparatus according to claim 9, characterized in that the nozzles of at least one group (40, 44, 48; 60, 62; 80, 82) can be supplied with fluid via a common pressure line.
11. (Cancelled) Apparatus according to one of the preceding claims, characterized in that the nozzles of at least one group (40, 44, 48; 60, 62; 80, 82) can be supplied with different fluids.

12. (Cancelled) Apparatus according to one of the preceding claims, characterized in that the nozzles of at least one group can be activated or deactivated individually or in sub groups.
13. (Cancelled) Apparatus according to one of the preceding claims, characterized in that the shape of the nozzle jet or stream and/or the flow volume of at least one nozzle of at least one group (40, 44, 48; 60, 62; 80, 82) can be varied.
14. (Cancelled) Apparatus according to one of the preceding claims, characterized in that a nozzle (52) is disposed on or in the region of the axis of rotation (A).
15. (Cancelled) Apparatus according to claim 14, characterized in that the nozzle (52) can be supplied with different fluids.
16. (Cancelled) Apparatus according to claim 15, characterized by at least two separate supply lines for different fluids.
17. (Cancelled) Apparatus according to one of the preceding claims, characterized in that respectively at least one group (40, 44, 48; 60, 62; 80, 82) of nozzles is provided above and below the substrate.
18. (Cancelled) Apparatus according to one of the preceding claims in combination with an apparatus according to one of the claims 31 to 43.

19. (Cancelled) Method for the treatment of disc-shaped substrates, especially semiconductor wafers, according to which the substrates are rotated about an axis of rotation that is disposed essentially perpendicular to the plane of the substrates, and via at least one first group of nozzles, which are differently spaced relative to the axis of rotation, a first fluid is applied, characterized in that the nozzles are controlled individually or in sub groups to achieve a selective treatment of surface regions of the substrate.
20. (Cancelled) Method according to claim 19, characterized in that for the termination of the treatment with the first fluid, at least one further fluid is conducted onto the substrate via at least one nozzle.
21. (Cancelled) Method according to claim 20, characterized in that ~~a~~the further fluid is conducted onto the substrate via at least one nozzle of at least one further group of nozzles.
22. (Cancelled) Method according to one of the claims 20 or 21, characterized in that ~~at least one~~ the further fluid is applied via a nozzle that is disposed closer to the axis of rotation than is a nozzle via which the first fluid is applied to the substrate, in order to displace the first fluid outwardly.
23. (Cancelled) Method according to claim 20, characterized in that nozzles that apply the first fluid are deactivated sequentially in a direction away from the axis of rotation or are switched over to the application of the second fluid.

24. (Cancelled) Method according to claim 21 or 22, characterized in that nozzles that apply the further fluid are activated sequentially in a direction away from the axis of rotation.
25. (Cancelled) Method according to one of the claims 20 to 24, characterized in that the further fluid is initially applied to the substrate in the region of the axis of rotation.
26. (Cancelled) Method according to one of the claims 19 to 25, characterized in that the treatment with the further fluid is terminated by applying a yet further fluid in the same manner as ~~is terminating~~ the treatment with the first fluid.
27. (Cancelled) Method according to one of the claims 19 to 26, characterized in that the first fluid is a treatment, cleaning, or rinsing liquid.
28. (Cancelled) Method according to one of the claims 20 to 27, characterized in that at least one further fluid is a rinsing liquid.
29. (Cancelled) Method according to one of the claims 20 to 28, characterized in that at least one further fluid is a fluid that reduces the surface tension of the fluid ~~found~~ present on the substrate.
30. (Cancelled) Method according to one of the claims 19 to 29, characterized by a simultaneous treatment of the upper side and the under side of the substrate.
31. (Cancelled) Apparatus for the treatment of disc-shaped substrates (3), especially semiconductor wafers, with an essentially planar carrier ring (5) that is rotatable about an

axis of rotation (A) via a rotation device in the plane, characterized by at least three support elements (8) that extend out of the plane of the carrier ring (5) and that form a multi-point support for the substrate (3) at a distance from the plane of the carrier ring (5).

- 32. (Cancelled) Apparatus according to claim 31, characterized in that support surfaces of the support elements (8) are disposed along a peripheral contour of the substrate (3).
- 33. (Cancelled) Apparatus according to claim 31 or 32, characterized in that the support elements extend into the region of a central opening (6) of the carrier ring (5).
- 34. (Cancelled) Apparatus according to one of the claims 31 to 33, characterized in that the support elements (8) extend from the inner periphery of the carrier ring (5).
- 35. (Cancelled) Apparatus according to one of the claims 31 to 34, characterized in that the support elements (8) extend at an incline relative to the plane of the carrier ring (5).
- 36. (Cancelled) Apparatus according to one of the claims 31 to 35, characterized in that the support surfaces (12) of the support elements (8) are inclined relative to the plane of the carrier ring (5).
- 37. (Cancelled) Apparatus according to one of the claims 31 to 36, characterized by at least two stop surfaces (20), which extend essentially perpendicular to the plane of the carrier ring (5), for limiting a lateral movement of the substrate (3).

38. (Cancelled) Apparatus according to claim 37, characterized in that the stop surfaces (20) are formed on the support elements (8).
39. (Cancelled) Apparatus according to claim 37, characterized in that the stop surfaces are provided on stop elements (27) that are provided separately from the support elements (8).
40. (Cancelled) Apparatus according to claim 39, characterized in that the stop elements (27) are movably disposed on the carrier ring (5) and are movable between a free position and a position contacting the substrate (3).
41. (Cancelled) Apparatus according to claim 39 or 40, characterized in that the stop elements (27) are movable into contact with the substrate (3) by a rotational movement of the carrier ring.
42. (Cancelled) Apparatus according to one of the claims 37 to 41, characterized in that the stop elements (27) have a cross-section that widens in an essentially V-shaped manner from the stop surfaces.
43. (Cancelled) Apparatus according to one of the claims 31 to 42, characterized in that the carrier ring (5) and the rotation device associated therewith, are disposed below the support surfaces of the support elements (8).

This listing of the following claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claims 1 – 43: Cancelled

44. (Previously Presented) An apparatus for treating disc-shaped substrates, comprising:

a device 10 for rotating said substrates 3 about an axis of rotation A; and

at least one first group of nozzles, 40, 60, 80, wherein the nozzles of said first group are differently spaced relative to said axis of rotation A, and wherein said nozzles are adapted to be controlled individually or in sub groups.

45. (Previously Presented) An apparatus according to claim 44, which comprises at least one further group of nozzles 44, 48; 62; 82, wherein the nozzles of said second group are differently spaced relative to said axis of rotation A.

46. (Previously Presented) An apparatus according to claim 45, wherein said nozzles of said second group are adapted to be controlled individually or in sub groups.

47. (Previously Presented) An apparatus according to claim 45, wherein three groups of nozzles 40, 44, 48 are provided.

48. (Previously Presented) An apparatus according to claim 45, wherein nozzles of at least one further group of nozzles 44, 48; 62; 82 are, with regard to their spacing relative to said axis of rotation A, offset relative to said nozzles of said at least one first group of nozzles 40, 60, 80.

49. (Currently Amended) An apparatus according to claim 45, wherein nozzles ~~of at~~ at least one group of nozzles 40, 44, 48; 60, 62; 80 are disposed along a straight line that extends radially relative to said axis of rotation A.

50. (Previously Presented) An apparatus according to claim 49, wherein said nozzles of at least two groups of nozzles 44, 48; 60, 62; 80, 82 are disposed along a common straight line.

51. (Previously Presented) An apparatus according to claim 50, wherein said nozzles of one group of nozzles 44, 48; 60, 62; 80, 82 are disposed between said nozzles of another group of nozzles 48, 44; 62, 60; 82, 80.

52. (Previously Presented) An apparatus according to claim 45, wherein said nozzles of at least one group of nozzles 40, 44, 48; 60, 62; 80, 82 are adapted to be supplied with fluid via a common fluid supply unit.

53. (Previously Presented) An apparatus according to claim 52, wherein said nozzles of at least one group of nozzles 40, 44, 48; 60, 62; 80, 82 are adapted to be supplied with fluid via a common pressure line.

54. (Previously Presented) An apparatus according to claim 45, wherein said nozzles of at least one group of nozzles 40, 44, 48; 60, 62; 80, 82 are adapted to be supplied with different fluids.

55. (Previously Presented) An apparatus according to claim 45, wherein said nozzles of at least one group of nozzles are adapted to be activated and deactivated individually or in sub groups.

56. (Currently) An apparatus according to claim 45, wherein at least one of a shape of a nozzle jet or stream, and a flow volume, of at least one nozzle of at least one group of nozzles 40, 44, 48, 60, 62, 80, 82 is adapted to be varied.

57. (Previously Presented) An apparatus according to claim 45, wherein a nozzle 52 is disposed on or in the vicinity of said axis of rotation A.

58. (Previously Presented) An apparatus according to claim 57, wherein said nozzle 52 is adapted to be supplied with different fluids.

59. (Previously Presented) An apparatus according to claim 58, wherein at least two separate feed lines are provided for different fluids.

60. (Previously Presented) An apparatus according to claim 45, wherein respectively at least one group of nozzles 40, 44, 48; 60, 62; 80, 82 is provided above and below a substrate.

61. (Previously Presented) An apparatus according to claim 44, which further comprises an essentially planar carrier ring, a rotation device for rotating said carrier ring in the plane thereof about said axis of rotation A, and at least three support elements 8, which extend out of said plane of said carrier ring 5, wherein said support elements 8 form a multi-point support for a substrate 3 at a distance from said carrier ring.

62. (Previously Presented) A method of treating disc-shaped substrates, including the steps of:

rotating said substrates 3 about an axis of rotation A that is disposed essentially perpendicular to a plane of said substrates;

providing at least one first group of nozzles 40, 60, 80, the nozzles of which are differently spaced relative to said axis of rotation A;

applying a first fluid to said substrates via said at least one first group of nozzles;
and

controlling said nozzles of said first group individually or in sub groups to achieve a selective treatment of surface regions of a substrate 3.

63. (Previously Presented) A method according to claim 62, wherein to terminate treatment with said first fluid, at least one further fluid is conducted onto said substrate via at least one nozzle.

64. (Previously Presented) A method according to claim 63, wherein said further fluid is conducted onto said substrate via at least one nozzle of a further group of nozzles.

65. (Previously Presented) A method according to claim 63, wherein said further fluid

is applied by a nozzle that is disposed closer to said axis of rotation than is a nozzle via which said first fluid is applied to said substrate in order to displace said first fluid outwardly.

66. (Previously Presented) A method according to claim 63, wherein nozzles that apply said first fluid are deactivated sequentially in a direction away from said axis of rotation, or are switched over to an application of said second fluid.

67. (Previously Presented) A method according to claim 64, wherein nozzles that apply said further fluid are activated sequentially in a direction away from said axis of rotation.

68. (Previously Presented) A method according to claim 63, wherein said further fluid is initially applied to said substrate in a vicinity of said axis of rotation.

69. (Previously Presented) A method according to claim 63, wherein treatment with said further fluid is terminated by applying a yet further fluid in the same manner as is the treatment with said first fluid.

70. (Previously Presented) A method according to claim 62, wherein said first fluid is a treatment liquid, a cleaning liquid, or a rinsing liquid.

71. (Previously Presented) A method according to claim 63, wherein said one further fluid is a rinsing liquid.

72. (Previously Presented) A method according to claim 63, wherein at least one further fluid is a fluid that reduces a surface tension of fluid found on said substrate.

73. (Previously Presented) A method according to claim 62, wherein an upper side and a lower side of said substrate are simultaneously treated.

74. (Previously Presented) An apparatus for treating disc-shaped substrates, comprising:

an essentially planar carrier ring;

a rotation device for rotating said carrier ring in the plane thereof about an axis of rotation; and

at least three support elements, which extend out of said plane of said carrier ring, wherein said support elements form a multi-point support for a substrate at a distance from said plane of said carrier ring.

75. (Previously Presented) An apparatus according to claim 74, wherein said support elements are provided with support surfaces that are disposed along a peripheral contour of said substrate.

76. (Previously Presented) An apparatus according to claim 74, wherein said support elements extend into a region of a central opening of said carrier ring.

77. (Previously Presented) An apparatus according to claim 74, wherein said support elements extend from an inner periphery of said carrier ring.

78. (Previously Presented) An apparatus according to claim 74, wherein said support elements extend at an incline relative to said plane of said carrier ring.

79. (Previously Presented) An apparatus according to claim 74, wherein support surfaces of said support elements are inclined relative to said plane of said carrier ring.

80. (Previously Presented) An apparatus according to claim 74, wherein at least two stop surfaces are provided that extend essentially perpendicular to said plane of said carrier ring and that serve for limiting a lateral movement of said substrate.

81. (Previously Presented) An apparatus according to claim 80, wherein said stop surfaces are formed on said support elements.

82. (Previously Presented) An apparatus according to claim 80, wherein said stop surfaces are provided on stop elements that are separate from said support elements.

83. (Previously Presented) An apparatus according to claim 82, wherein said stop elements are movably disposed on said carrier ring and are movable between a free position and a position where they contact said substrate.

84. (Previously Presented) An apparatus according to claim 82, wherein said stop

elements are movable into contact with said substrate by means of a rotational movement of said carrier ring.

85. (Previously Presented) An apparatus according to claim 80, wherein said stop elements have a cross-sectional configuration that widens in an essentially V-shaped manner in a direction away from said stop surfaces.

86. (Previously Presented) An apparatus according to claim 74, wherein said carrier ring, and said rotation device that is associated therewith, are disposed below support surfaces of said support elements.